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## Supporting information

## Highly selective photocatalytic oxidation of 5-hydroxymethylfurfural

## by interfacial Pt-O bonding Pt-Ov-BiOBr

Ming Gong,<sup>a</sup> Hui Zhao,<sup>a</sup> Chengsi Pan,<sup>a</sup> Yuming Dong,<sup>\*a</sup> Yingxin Guo,<sup>a</sup> Haixia Li,<sup>a</sup> Jiawei Zhang,<sup>a</sup> Guangli Wang,<sup>a</sup> and Yongfa Zhu<sup>b</sup>

a. International Joint Research Center for Photoresponsive Molecules and Materials, School of Chemical and Material Engineering, Jiangnan University, Wuxi 214122, China.

b. Department of Chemistry, Tsinghua University, Beijing 100084, China.

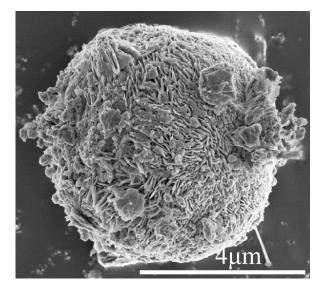


Fig. S1 SEM diagrams of Ov-BiOBr

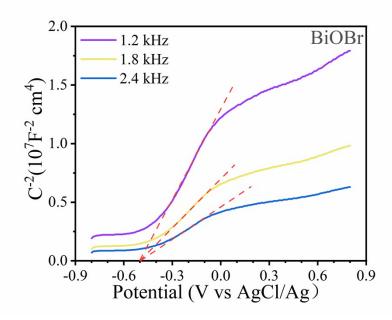


Fig. S2 Motschottky curve of BiOBr

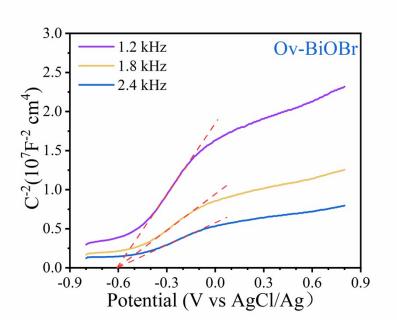


Fig. S3 Motschottky curve of Ov-BiOBr

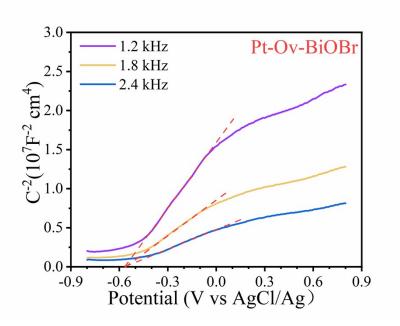


Fig. S4 Motschottky curve of Pt-Ov-BiOBr

The band edge positions of catalysts. can be calculated using the following equation:

$$E_{CB} (V vs. NHE) = E_{fb} (V vs. AgCl/Ag) + 0.197 - X_{-----} Eq. s1$$
$$E_{VB} = E_{CB} + E_{g-----} Eq. s2$$

Where  $E_{VB}$  and  $E_{cB}$  stand for the valence band edge potential and conduction band edge potential, respectively;  $E_{AgCl/Ag}=0.197V$  (saturated potassium chloride) vs. NHE; X is the voltage difference between the conduction band value and the flat potential value, generally 0.1-0.2 eV (the conduction bands of n-type semiconductors are normally 0.1-0.2 eV deeper than the flat-band potential). Therefore, the conduction band position is obtained by subtracting 0.3eV from the potential of each flat band.

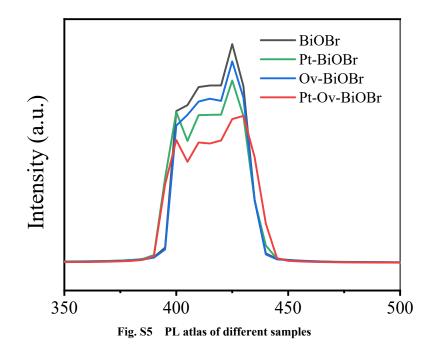


Table S1	XPS	ratio	of	each	sample
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Sample	Ov ratio	Bi <sup>(3-x)+</sup> ratio	Pt <sup>2+</sup> ratio
Pt-BiOBr			12.8
Ov-BiOBr	24.29	5.16	
Pt-Ov-BiOBr	32.6	11.82	25.9